What is claimed is:

1. An In-Plane switching mode liquid crystal display (LCD) device comprising:

lower and upper substrates;

gate and data lines crossing each other on the lower substrate to define a pixel region;

a plurality of first common electrodes diverging in the pixel region at fixed intervals;

a first pixel electrode in the pixel region between the first common electrodes;

second common electrodes and second pixel electrodes on the upper substrate respectively corresponding to the first common electrodes and the first pixel electrodes on the lower substrate; and

a liquid crystal layer between the lower and upper substrates.

2. The In-Plane switching mode LCD device of claim 1, further comprising a conductive bar electrically connecting the first and second pixel electrodes to each other.

3. The In-Plane switching mode LCD device of claim 2, wherein the conductive bar is formed of any one of Ag, Al, and an Al alloy.

4. The In-Plane switching mode LCD device of claim 1, wherein the same voltage is applied to the first and second common electrodes from an external driving circuit.

5. The In-Plane switching mode LCD device of claim 1, further comprising Ag dot for connecting the first and second common electrodes to each other.

6. The In-Plane switching mode LCD device of claim 1, wherein the first common electrode is formed on the different layer from the first pixel electrode.

7. The In-Plane switching mode LCD device of claim 1, further comprising a thin film transistor adjacent a crossing of the gate and data lines.

8. The In-Plane switching mode LCD device of claim 1, further comprising:

a black matrix layer on specific portions of the upper substrate except for the pixel regions of the lower substrate; and

a color filter layer on the portions of the upper substrate corresponding to the respective pixel regions of the lower substrate.

9. The In-Plane switching mode LCD device of claim 1, wherein the first common electrode is formed in the same layer as the gate line or data line.

10. The In-Plane switching mode LCD device of claim 1, wherein an electric field parallel to the lower and upper substrates is formed between the first common electrode and the first pixel electrode, and an electric field parallel to the lower and upper substrates is formed

between the second common electrode and the second pixel electrode when applying the voltage to the respective electrodes of the lower and upper substrates.

11. The In-Plane switching mode LCD device of claim 1, wherein the first and second common electrodes and the first and second pixel electrodes are formed of any one of Cu, Cr, Mo, Al, Ti, Ta and Al alloy.

12. The In-Plane switching mode LCD device of claim 1, wherein the first and second common electrodes and the first and second pixel electrodes are formed of any one of indium oxide, zinc oxide, indium-tin-oxide, tin-antimony-oxide, zinc-aluminum-oxide, and indium-zinc-oxide.

13. A method for manufacturing an In-Plane switching mode liquid crystal display (LCD) device comprising the steps of:

preparing lower and upper substrates;

forming gate and data lines crossing each other on the lower substrate to define a pixel region;

forming a plurality of first common electrodes diverging in the pixel region at fixed intervals;

forming a first pixel electrode in the pixel region between the first common electrodes;

forming a second common electrode on the upper substrate corresponding to the first common electrode;

forming a second pixel electrode on the upper substrate corresponding to the first pixel electrode; and

forming a liquid crystal layer between the lower and upper substrates.

14. The method of claim 13, further comprising the step of forming a conductive bar on the first pixel electrode to electrically connect the first and second pixel electrodes to each other.

15. The method of claim 14, wherein the conductive bar is formed of any one of Ag, Al, and an Al alloy.

16. The method of claim 13, wherein the same common voltage is directly applied to the first and second common electrodes from an external driving circuit.

17. The method of claim 16, further comprising the step of forming an Ag dot in the outermost portion of the lower and upper substrates to connect the first and second common electrodes to each other.

18. The method of claim 13, wherein the first common electrode is formed on the different layer from the first pixel electrode according as an insulating layer is interposed between the first common electrode and the first pixel electrode.

19. The method of claim 13, further comprising the step of forming a thin film transistor adjacent to a crossing of the gate and data lines.

20. The method of claim 13, wherein the first common electrode is formed on the same layer as the gate or data line.

21. The method of claim 13, wherein the first and second common electrodes and the first and second pixel electrodes are formed of any one of Cu, Cr, Mo, Al, Ti, Ta, and an Al alloy.

22. The method of claim 13, wherein the first and second common electrodes and the first and second pixel electrodes are formed of any one of indium oxide, zinc oxide, indium-tin-oxide, tin-antimony-oxide, zinc-aluminum-oxide, or indium-zinc-oxide.